

**Amendments to the Abstract**

Please replace the abstract of the disclosure with the following amended/new abstract of the disclosure:

A magnetoresistive solid-state storage device (MRAM) performs error correction coding (ECC) of stored information. Since currently available MRAM devices are subject to physical failures, data storage arrangements are described to ~~minimise~~ minimize the affect of those failures on the stored ECC encoded data, including storing all bits of each symbol in storage cells 16 in one row 12 (Figure 3), or in at least two rows 12 but using storage cells 16 in the same columns 14 (Figure 4). Sets of bits taken from each row 12 are allocated to different codewords 204 (Figure 5) and the order of allocation can be rotated (Figure 6). A second level of error checking can be applied by adding a parity bit 226 to each symbol 206 (Figure 7).